



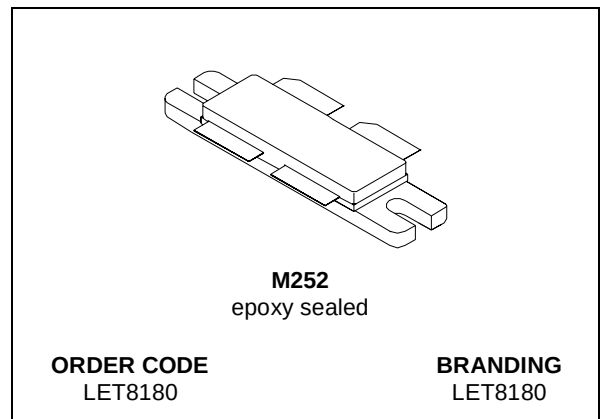
LET8180

RF POWER TRANSISTORS *Ldmos Enhanced Technology*

TARGET DATA

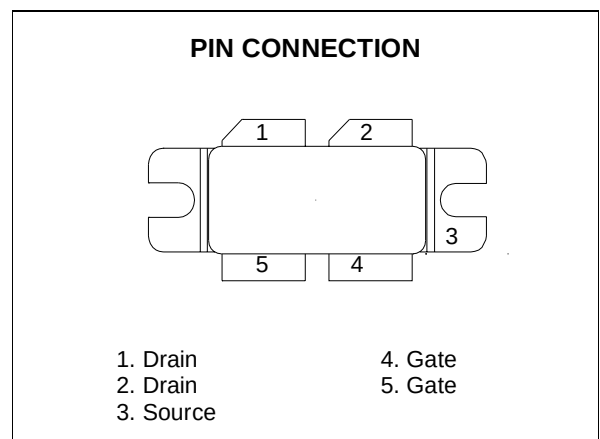
N-CHANNEL ENHANCEMENT-MODE LATERAL MOSFETs

- EXCELLENT THERMAL STABILITY
- COMMON SOURCE CONFIGURATION, PUSH-PULL
- $P_{OUT} = 220\text{ W}$ with 17 dB TYP. gain @ 860 MHz
- BeO FREE PACKAGE
- INTERNAL INPUT MATCHING
- ESD PROTECTION



DESCRIPTION

The LET8180 is a common source N-Channel enhancement-mode lateral Field-Effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 1.0 GHz. The LET8180 is designed for high gain and broadband performance operating in common source mode at 32 V. Its internal matching makes it ideal for base station applications requiring high linearity.



ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25\text{ }^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
$V_{(BR)DSS}$	Drain-Source Voltage	65	V
V_{GS}	Gate-Source Voltage	-0.5 to +15	V
I_D	Drain Current	18	A
P_{DISS}	Power Dissipation (@ $T_c = +70\text{ }^{\circ}\text{C}$)	289	W
T_j	Max. Operating Junction Temperature	200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{th(j-c)}$	Junction -Case Thermal Resistance	0.45	$^{\circ}\text{C/W}$
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LET8180

ELECTRICAL SPECIFICATION ($T_{CASE} = 25^{\circ}C$)

STATIC (Per Section)

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$	$I_D = 10\text{ }\mu\text{A}$	65			V
I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 32\text{ V}$			10	μA
I_{GSS}	$V_{GS} = 5\text{ V}$	$V_{DS} = 0\text{ V}$			1	μA
$V_{GS(Q)}$	$V_{DS} = 32\text{ V}$	$I_D = \text{TBD}$	2.5		4.5	V
$V_{DS(ON)}$	$V_{GS} = 10\text{ V}$	$I_D = 3\text{ A}$		0.28	0.45	V
G_{FS}	$V_{DS} = 10\text{ V}$	$I_D = 3\text{ A}$		2.6		mho
C_{ISS}^*	$V_{GS} = 0\text{ V}$	$V_{DS} = 32\text{ V}$		TBD		pF
C_{OSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 32\text{ V}$			70	pF
C_{RSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 32\text{ V}$		2.5		pF

* Includes Internal Input Moscap.

Symbol	Test Conditions	Min.	Typ.	Max.	Unit
DYNAMIC ($f = 860\text{ MHz}$)					
$P_{OUT}^{(1)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$	200	220		W
$\eta_D^{(1)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$	50	60		%
$G_P^{(2)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$ $P_{OUT} = 200\text{ W PEP}$	16	17		dB
$\text{IMD3}^{(2)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$ $P_{OUT} = 200\text{ W PEP}$		-31		dBc
Load mismatch	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$ $P_{OUT} = 200\text{ W}$ ALL PHASE ANGLES	10:1			VSWR
DYNAMIC ($f = 470 - 860\text{ MHz}$)					
$P_{OUT}^{(1)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$	180			W
$\eta_D^{(1)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$	50			%
$G_P^{(1)}$	$V_{DD} = 32\text{ V}$ $I_{DQ} = \text{TBD}$	14.5			dB

(1) 1 dB Compression point

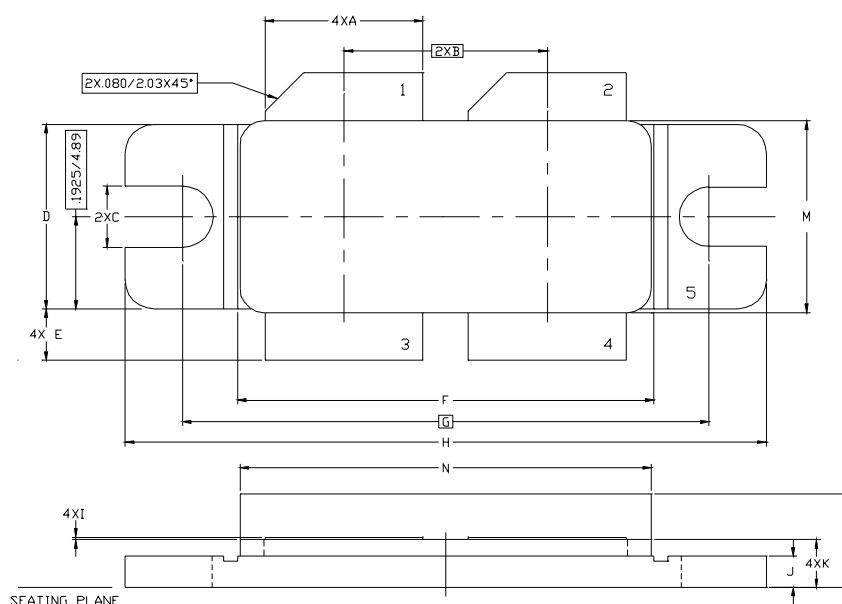
(2) $f_1 = 860\text{ MHz}$, $f_2 = 860.1\text{ MHz}$

ESD PROTECTION CHARACTERISTICS

Test Conditions	Class
Human Body Model	2
Machine Model	M3

M252 (.400 x .860 4L BAL N/HERM W/FLG) MECHANICAL DATA

DIM.	mm			Inch		
	MIN.	TYP.	MAX	MIN.	TYP.	MAX
A	8.13		8.64	.320		.340
B		10.80			.425	
C	3.00		3.30	.118		.130
D	9.65		9.91	.380		.390
E	2.16		2.92	.085		.115
F	21.97		22.23	.865		.875
G		27.94			1.100	
H	33.91		34.16	1.335		1.345
I	0.10		0.15	.004		.006
J	1.52		1.78	.060		.070
K	2.36		2.74	.093		.108
L	4.57		5.33	.180		.210
M	9.96		10.34	.392		.407
N	21.64		22.05	.852		.868



Controlling dimension: Inches

1022783C

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